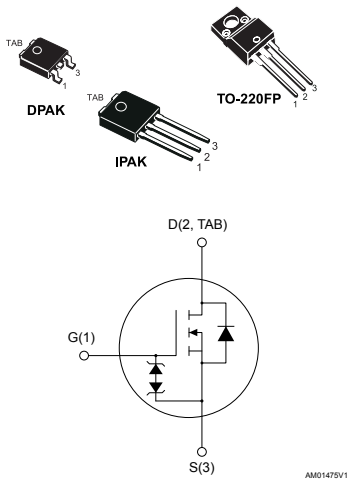


N-channel 620 V, 2.9 Ω typ., 2.2 A MDmesh™ K3 Power MOSFETs in DPAK, TO-220FP and IPAK packages



AM01475V1

Features

Order code	V_{DS}	$R_{DS(on)max.}$	I_D	Package
STD2N62K3	620 V	3.6 Ω	2.2 A	DPAK
STF2N62K3				TO-220FP
STU2N62K3				IPAK

- 100% avalanche tested
- Extremely high dv/dt capability
- Very low intrinsic capacitance
- Improved diode reverse recovery characteristics
- Zener-protected

Applications

- Switching applications

Description

These MDmesh™ K3 Power MOSFETs are the result of improvements applied to STMicroelectronics' MDmesh™ technology, combined with a new optimized vertical structure. These devices boast an extremely low on-resistance, superior dynamic performance and high avalanche capability, rendering them suitable for the most demanding applications.

Product status link

[STD2N62K3](#)
[STF2N62K3](#)
[STU2N62K3](#)

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value			Unit
		DPAK	TO-220FP	IPAK	
V_{DS}	Drain-source voltage	620			V
V_{GS}	Gate-source voltage	±30			V
I_D	Drain current (continuous) at $T_C = 25\text{ °C}$	2.2	2.2 ⁽¹⁾	2.2	A
I_D	Drain current (continuous) at $T_C = 100\text{ °C}$	1	1 ⁽¹⁾	1	A
$I_{DM}^{(2)}$	Drain current (pulsed)	8.8			A
P_{TOT}	Total dissipation at $T_C = 25\text{ °C}$	45	20	45	W
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat-sink ($t = 1\text{ s}$, $T_C = 25\text{ °C}$)	-	2500	-	V
$dv/dt^{(3)}$	Peak diode recovery voltage slope	12			V/ns
T_J	Operating junction temperature range	-55 to 150			°C
T_{stg}	Storage temperature range				

- Limited by maximum junction temperature.
- Pulse width limited by safe operating area.
- $I_{SD} \leq 2.2\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{D\text{peak}} \leq V_{(BR)DSS}$, $V_{DD} = 80\% V_{(BR)DSS}$.

Table 2. Thermal data

Symbol	Parameter	Value			Unit
		DPAK	TO-220FP	IPAK	
$R_{thj\text{-case}}$	Thermal resistance junction-case	2.78	6.25	2.78	°C/W
$R_{thj\text{-amb}}$	Thermal resistance junction-ambient		62.5	100	°C/W
$R_{thj\text{-pcb}}^{(1)}$	Thermal resistance junction-pcb	50			°C/W

- When mounted on 1inch² FR-4 board, 2 oz Cu.

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
$I_{AR}^{(1)}$	Avalanche current, repetitive or not-repetitive	2.2	A
$E_{AS}^{(2)}$	Single pulse avalanche energy	85	mJ

- Pulse width limited by T_J max.
- Starting $T_J = 25\text{ °C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$.

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0\text{ V}$	620			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 620\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 620\text{ V}$, $T_C = 125\text{ °C}$ ⁽¹⁾			50	μA
I_{GSS}	Gate body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 50\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 1.1\text{ A}$		2.9	3.6	Ω

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 50\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	340	-	μF
C_{oss}	Output capacitance			26		
C_{rss}	Reverse transfer capacitance			4		
$C_{o(tr)}$ ⁽¹⁾	Equivalent capacitance time related	$V_{DS} = 0\text{ to }496\text{ V}$, $V_{GS} = 0\text{ V}$	-	17	-	μF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	5	-	Ω
Q_g	Total gate charge	$V_{DD} = 496\text{ V}$, $I_D = 2.2\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 17. Test circuit for gate charge behavior)	-	15	-	nC
Q_{gs}	Gate-source charge			3		
Q_{gd}	Gate-drain charge			9		

1. $C_{o(tr)}$ is a constant capacitance value that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 310\text{ V}$, $I_D = 1.1\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 16. Test circuit for resistive load switching times and Figure 21. Switching time waveform)	-	8	-	ns
t_r	Rise time			4.4		
$t_{d(off)}$	Turn-off delay time			21		
t_f	Fall time			22		

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		2.2	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				8.8	
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 2.2 \text{ A}, V_{GS} = 0 \text{ V}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 2.2 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$	-	200		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 60 \text{ V}$ (see Figure 18. Test circuit for inductive load switching and diode recovery times)		0.9		μC
I_{RRM}	Reverse recovery current			9		A
t_{rr}	Reverse recovery time	$I_{SD} = 2.2 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$	-	240		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 60 \text{ V}, T_j = 150 \text{ }^\circ\text{C}$ (see Figure 18. Test circuit for inductive load switching and diode recovery times)		1.15		μC
I_{RRM}	Reverse recovery current			10		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

Table 8. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1 \text{ mA}, I_D = 0 \text{ A}$	± 30			V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

2.1 Electrical characteristics curves

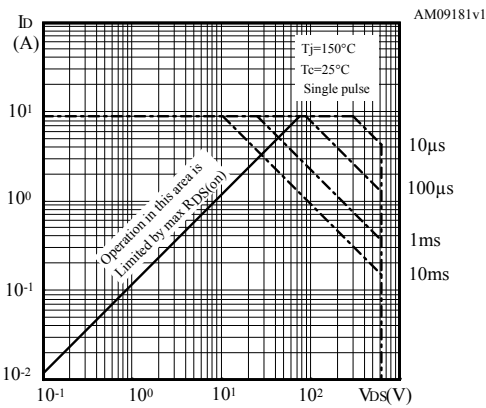
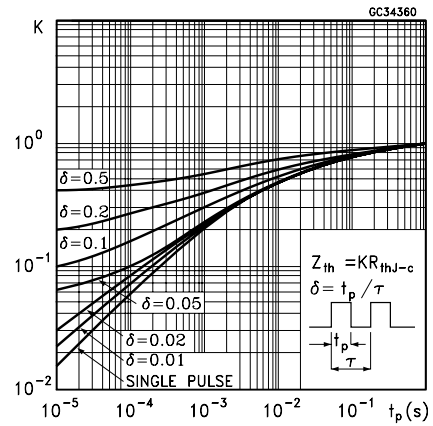
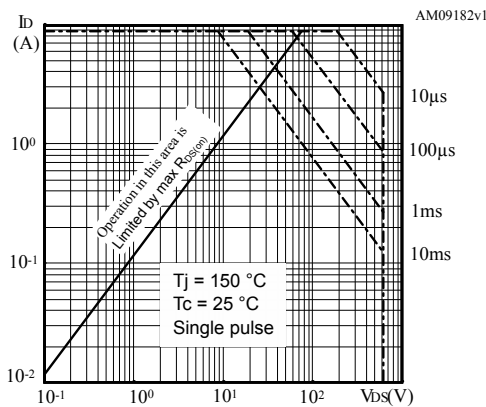
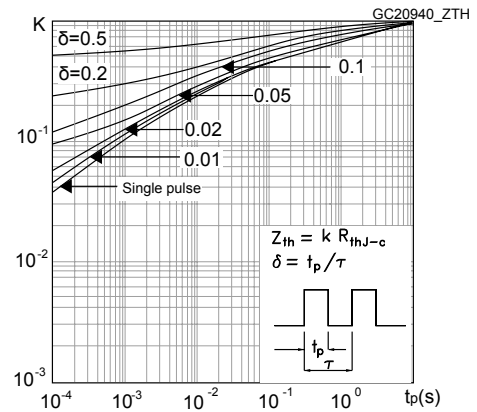
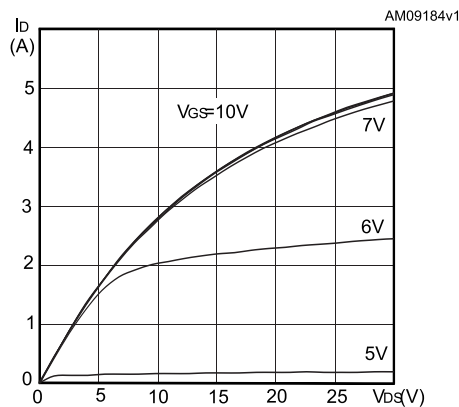
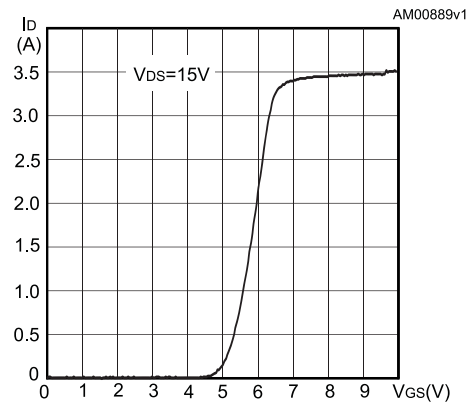
Figure 1. Safe operating area for DPAK and IPAK

Figure 2. Thermal impedance for DPAK and IPAK

Figure 3. Safe operating area for TO-220FP

Figure 4. Thermal impedance for TO-220FP

Figure 5. Output characteristics

Figure 6. Transfer characteristics


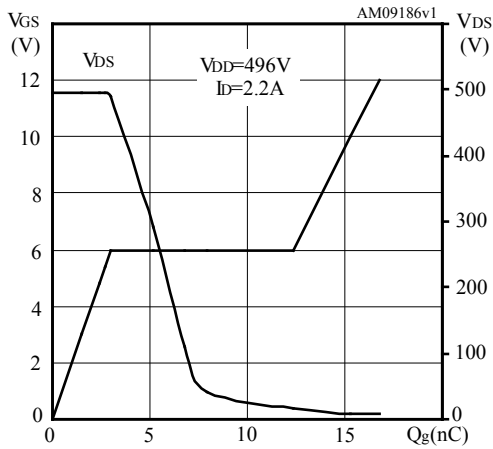
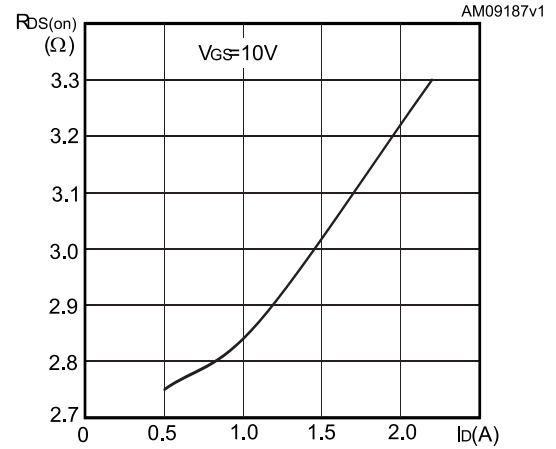
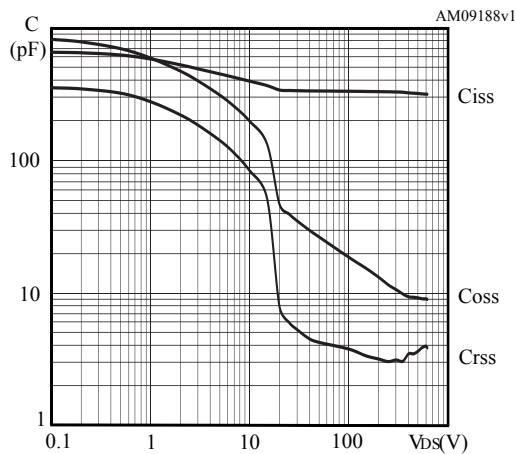
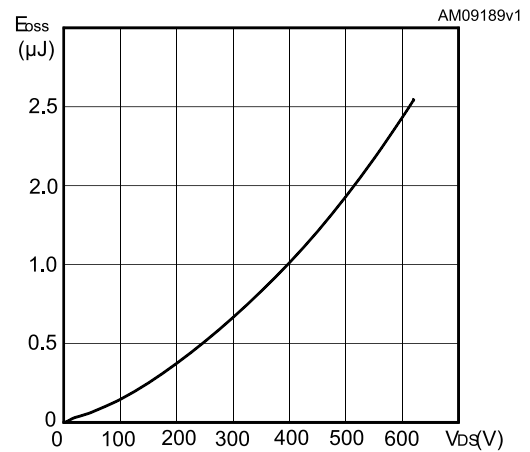
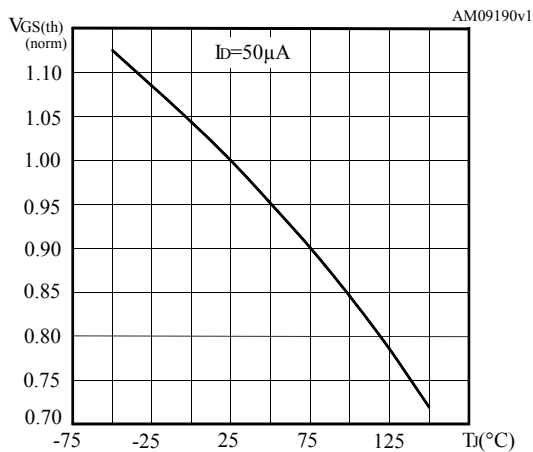
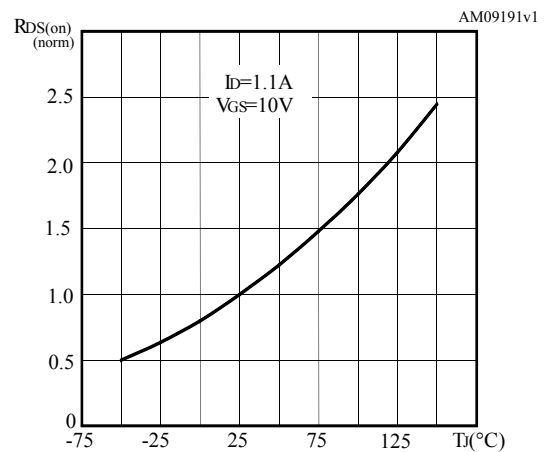
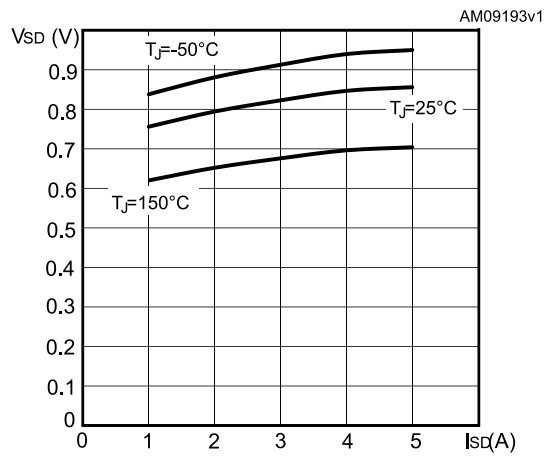
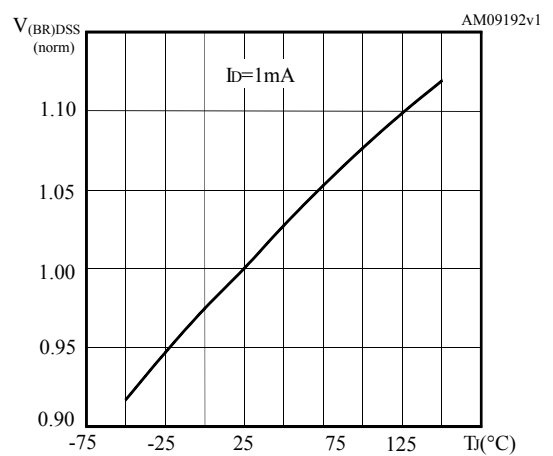
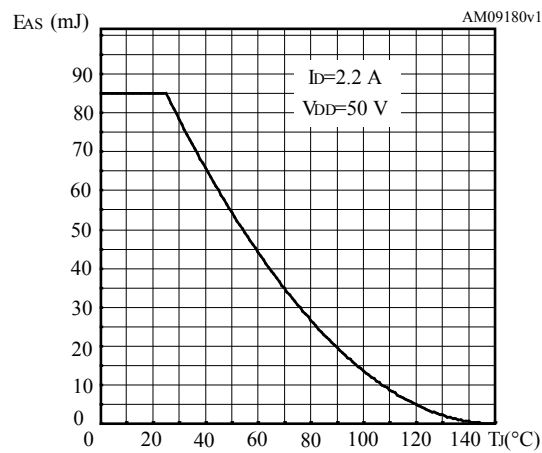
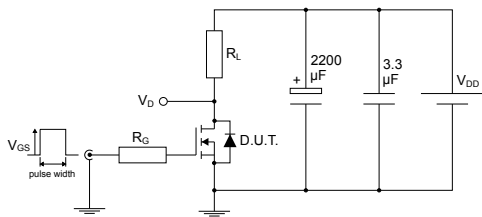
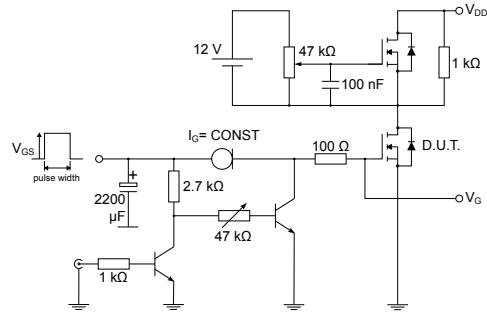
Figure 7. Gate charge vs gate-source voltage

Figure 8. Static drain-source on-resistance

Figure 9. Capacitance variations

Figure 10. Output capacitance stored energy

Figure 11. Normalized gate threshold voltage vs temperature

Figure 12. Normalized on-resistance vs temperature


Figure 13. Source-drain diode forward characteristics

Figure 14. Normalized $V_{(BR)DSS}$ vs temperature

Figure 15. Maximum avalanche energy vs starting T_j


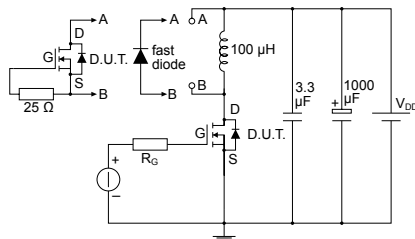
3 Test circuits

Figure 16. Test circuit for resistive load switching times


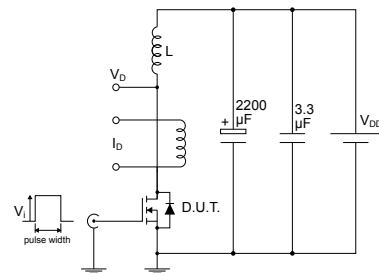
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Figure 17. Test circuit for gate charge behavior


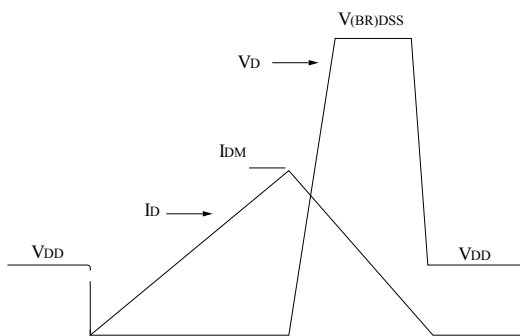
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Figure 18. Test circuit for inductive load switching and diode recovery times


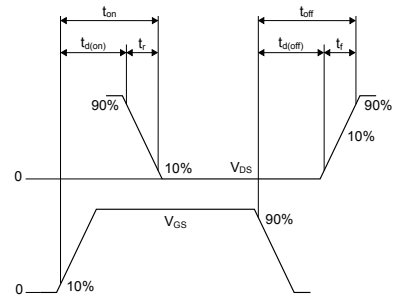
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Figure 19. Unclamped inductive load test circuit


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Figure 20. Unclamped inductive waveform


AM01472v1

Figure 21. Switching time waveform


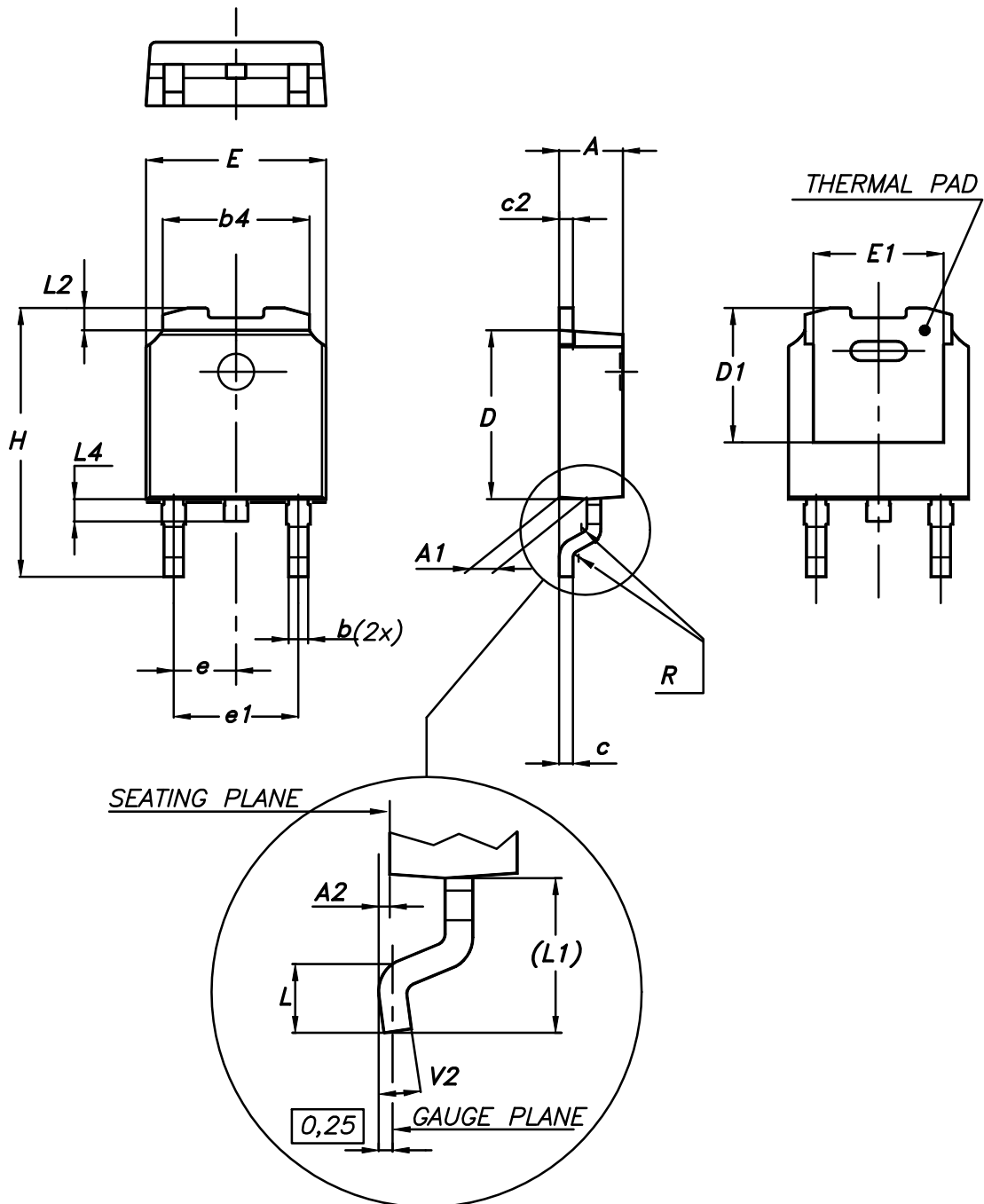
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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 DPAK (TO-252) type A package information

Figure 22. DPAK (TO-252) type A package outline



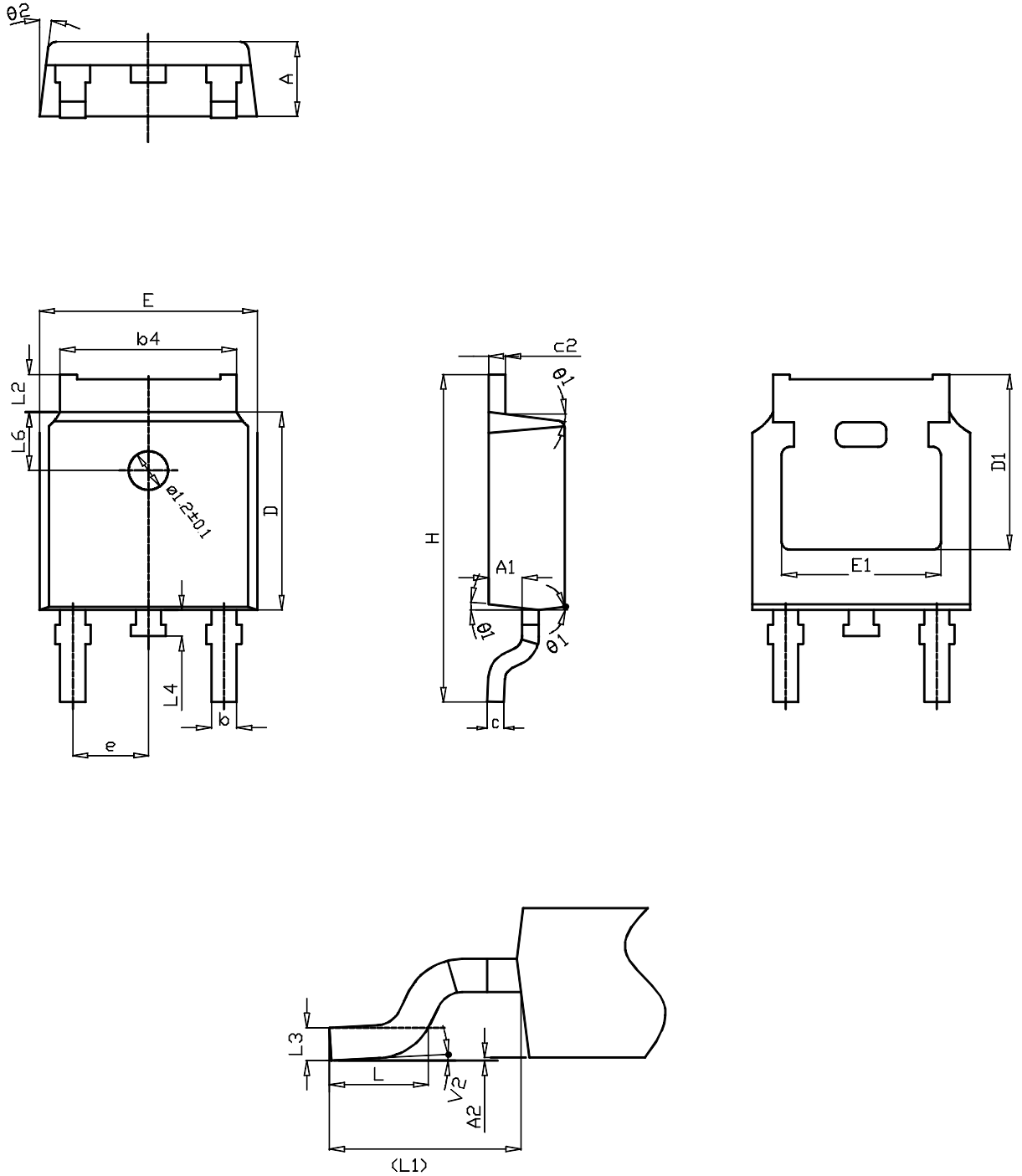
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Table 9. DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

4.2 DPAK (TO-252) type C package information

Figure 23. DPAK (TO-252) type C package outline



0068772_C_25

Table 10. DPAK (TO-252) type C mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.25		
E	6.50	6.60	6.70
E1	4.70		
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.90		1.25
L3	0.51 BSC		
L4	0.60	0.80	1.00
L6	1.80 BSC		
θ1	5°	7°	9°
θ2	5°	7°	9°
V2	0°		8°

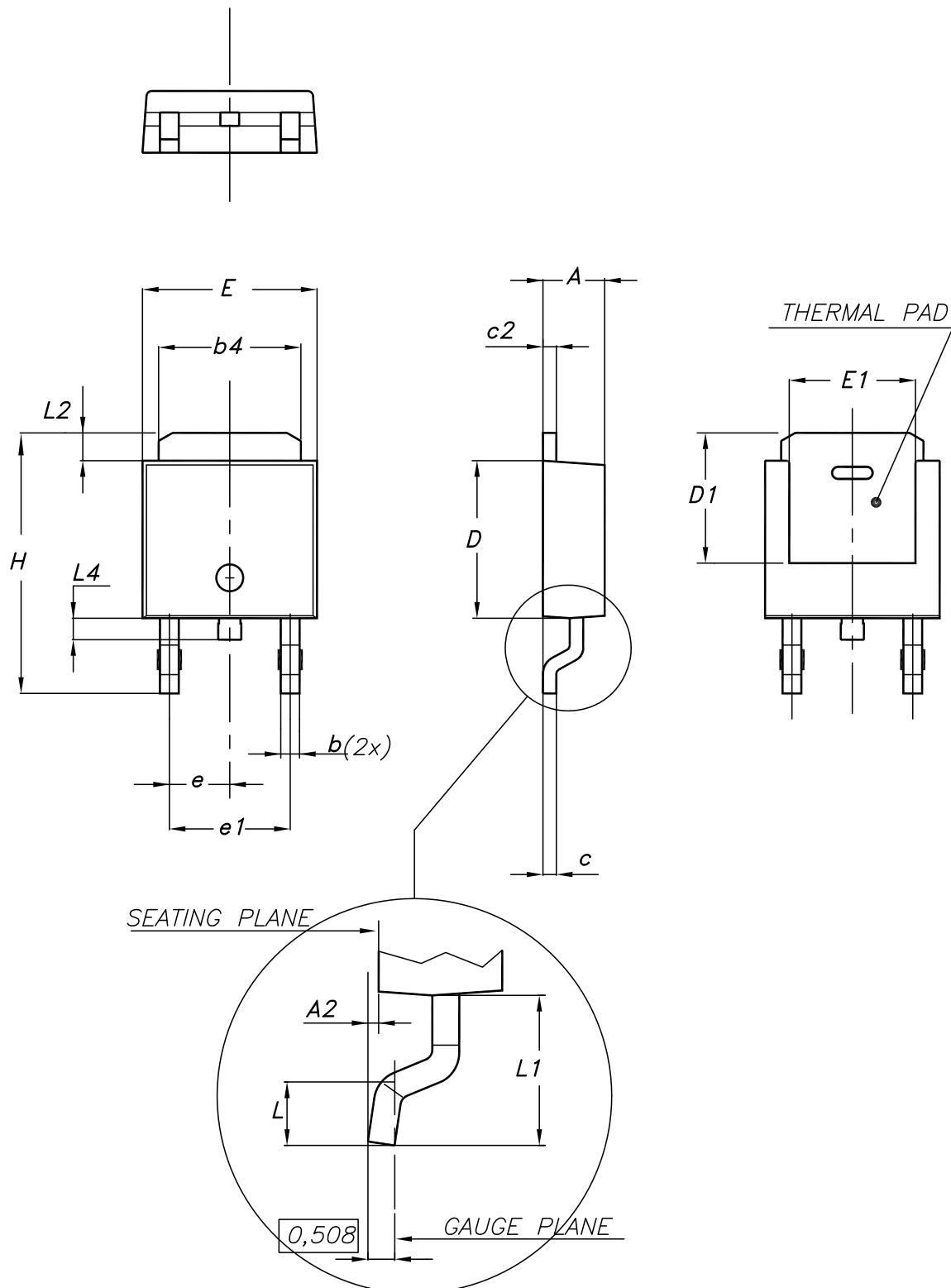
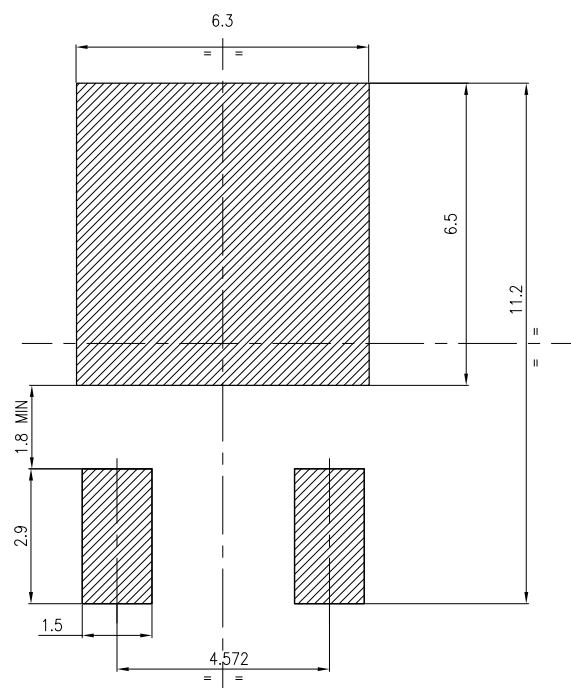
4.3 DPAK (TO-252) type E package information
Figure 24. DPAK (TO-252) type E package outline


Table 11. DPAK (TO-252) type E mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.18		2.39
A2			0.13
b	0.65		0.884
b4	4.95		5.46
c	0.46		0.61
c2	0.46		0.60
D	5.97		6.22
D1	5.21		
E	6.35		6.73
E1	4.32		
e		2.286	
e1		4.572	
H	9.94		10.34
L	1.50		1.78
L1		2.74	
L2	0.89		1.27
L4			1.02

Figure 25. DPAK (TO-252) recommended footprint (dimensions are in mm)


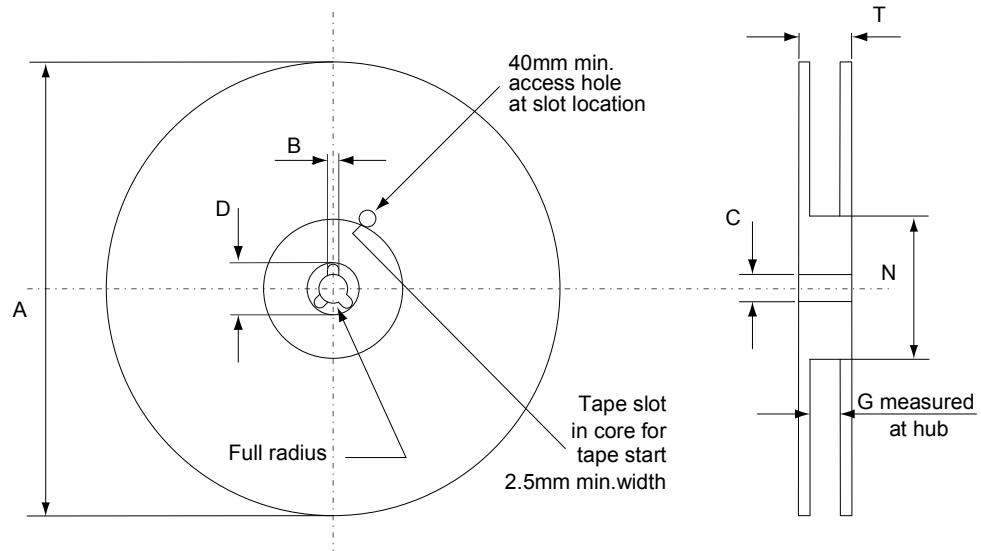
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4.4 DPAK (TO-252) packing information

Figure 26. DPAK (TO-252) tape outline



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Figure 27. DPAK (TO-252) reel outline


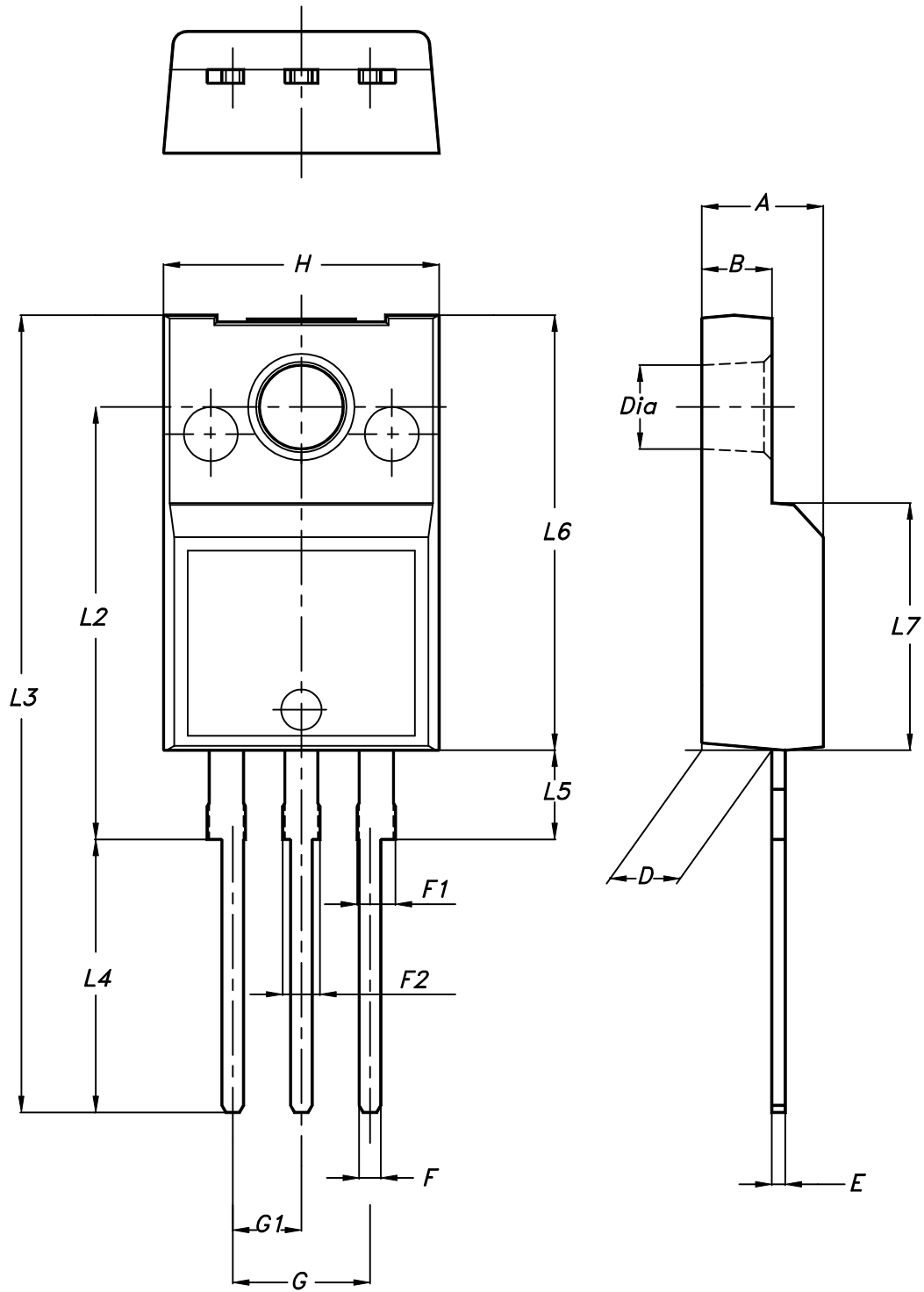
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Table 12. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

4.5 TO-220FP package information

Figure 28. TO-220FP package outline



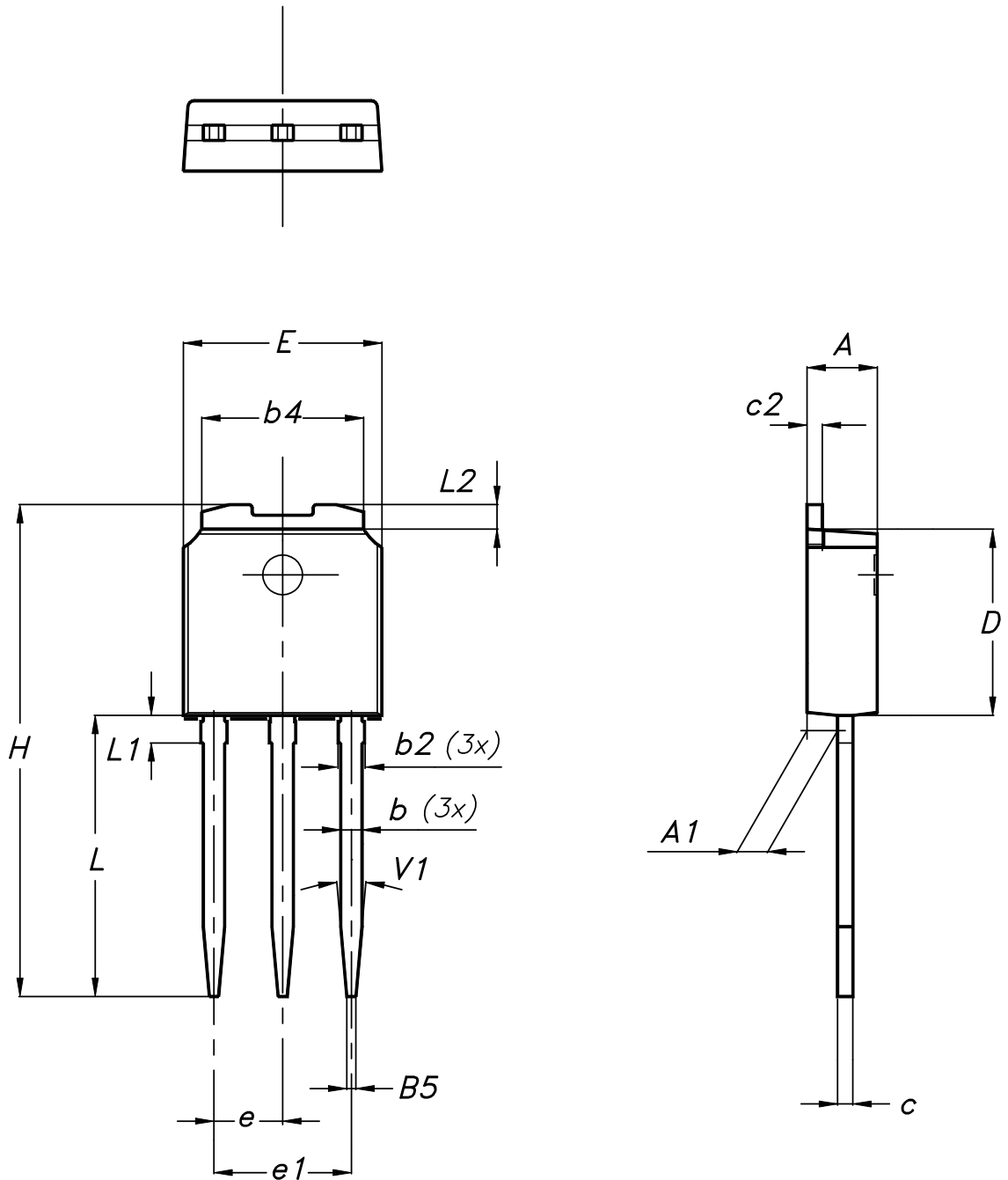
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Table 13. TO-220FP package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

4.6 IPAK (TO-251) type A package information

Figure 29. IPAK (TO-251) type A package outline



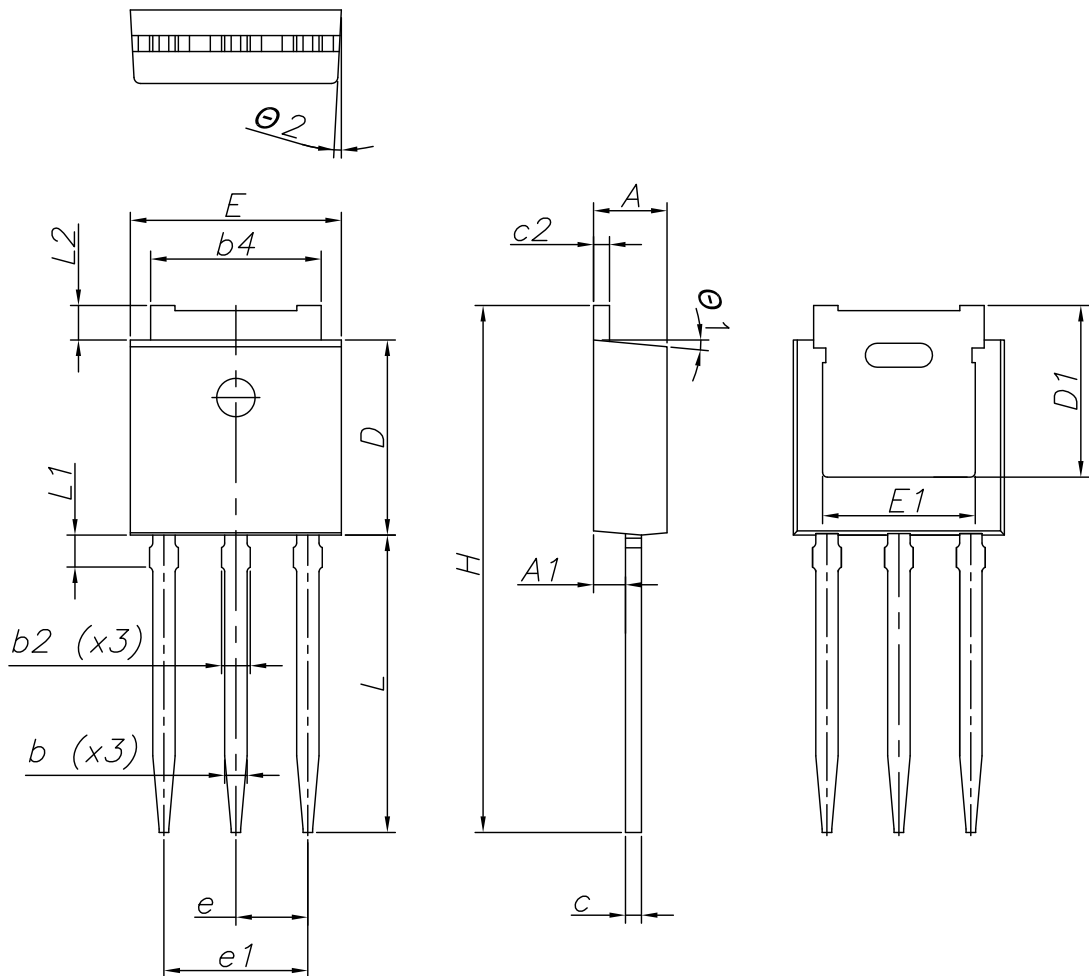
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Table 14. IPAK (TO-251) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

4.7 IPAK (TO-251) type C package information

Figure 30. IPAK (TO-251) type C package outline



0068771_IK_typeC_rev14

Table 15. IPAK (TO-251) type C package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.35
A1	0.90	1.00	1.10
b	0.66		0.79
b2			0.90
b4	5.23	5.33	5.43
c	0.46		0.59
c2	0.46		0.59
D	6.00	6.10	6.20
D1	5.20	5.37	5.55
E	6.50	6.60	6.70
E1	4.60	4.78	4.95
e	2.20	2.25	2.30
e1	4.40	4.50	4.60
H	16.18	16.48	16.78
L	9.00	9.30	9.60
L1	0.80	1.00	1.20
L2	0.90	1.08	1.25
θ1	3°	5°	7°
θ2	1°	3°	5°

5 Ordering information

Table 16. Order codes

Order code	Marking	Package	Packing
STD2N62K3	2N62K3	DPAK	Tape and reel
STF2N62K3		TO-220FP	Tube
STU2N62K3		IPAK	

Revision history

Table 17. Document revision history

Date	Version	Changes
31-May-2011	1	First release
20-Mar-2012	2	Added new package: D ² PAK – Table 1: Device summary, Section 4: Package mechanical data and Section 5: Packaging mechanical data have been modified. Minor text changes.
04-Jun-2018	3	The part numbers STB2N62K3 and STP2N62K3 have been moved to a separate datasheet. Removed maturity status indication from cover page. The document status is production data. Updated title and features in cover page. Updated Section 1 Electrical ratings , Section 2 Electrical characteristics , Section 2.1 Electrical characteristics curves and Section 4 Package information . Minor text changes.

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